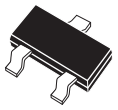
CMPD7000

DUAL SILICON SWITCHING DIODE
SERIES CONNECTION



SOT-23 CASE

Central™
Semiconductor Corp.

DESCRIPTION:
The CENTRAL SEMICONDUCTOR CMPD7000 type is a ultra-high speed silicon switching diode manufactured by the epitaxial planar process, in an epoxy molded surface mount package, connected in a series configuration, designed for high speed switching applications.

MARKING CODE: C5C

MAXIMUM RATINGS: (T_A=25℃)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Average Forward Current	I_O	200	mA
Peak Forward Current	I_{FM}	500	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
BV_R	I_R=100μA	100			V
I_R	V_R=50V			300	nA
I_R	V_R=50V, T_A=125°C			100	μA
I_R	V_R=100V			500	nA
V_F	I_F=1.0mA	0.55		0.70	V
V_F	I_F=10mA	0.67		0.82	V
V_F	I_F=100mA	0.75		1.10	V
C_T	V_R=0, f=1.0 MHz			1.5	pF
t_{rr}	I_R=I_F=10mA, R_L=100Ω, Rec. to 1.0mA		2.0	4.0	ns

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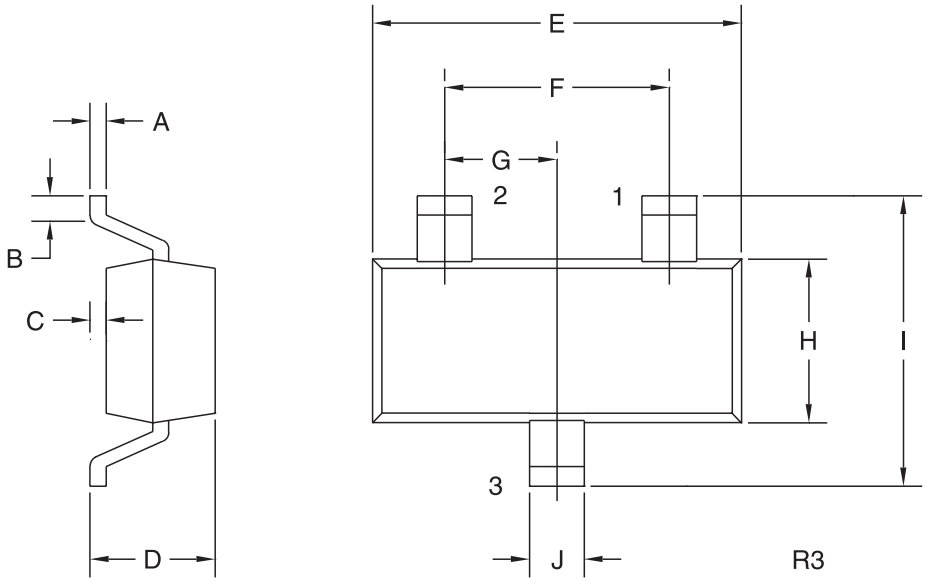
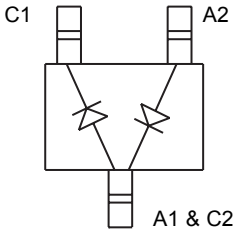
CMPD7000

DUAL SILICON SWITCHING DIODE
SERIES CONNECTION

SOT-23 CASE - MECHANICAL OUTLINE





MARKING CODE: C5C

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

R4 (26-September 2002)